

IN THE SPECIFICATION:

(1) Kindly add the following sentence at the conclusion of the paragraph ending on page 19, line 8, of the as-filed Application:

--Turning briefly to FIGURE 3C, illustrated is an embodiment of the invention wherein the silicon carbide tub 310 of FIGURE 3B is located within a trench in the conductive substrate 305. In this embodiment, a tub 335, 340 of the CMOS device comprises a material different from the silicon carbide tub 310.

IN THE CLAIMS:

Claims 1-43 (Canceled)

44. (Previously Presented) A semiconductor device, comprising:
a lateral metal-oxide semiconductor field effect transistor (MOSFET), including:
 a silicon carbide tub located within a trench formed in a conductive substrate;
 a gate formed on the silicon carbide tub; and
 source and drain regions located in the silicon carbide tub and laterally offset from
the gate; and
a complimentary metal-oxide semiconductor (CMOS) device formed on the conductive
substrate, the CMOS device having a tub comprising a material different from the silicon carbide
tub.